

## Silicon Diffused Power Transistor

BUT11AI

## GENERAL DESCRIPTION

Enhanced performance, high speed switching npn transistor in TO220AB envelope specially suited for high frequency electronic lighting ballast applications and converters, inverters, switching regulators, motor control systems etc.

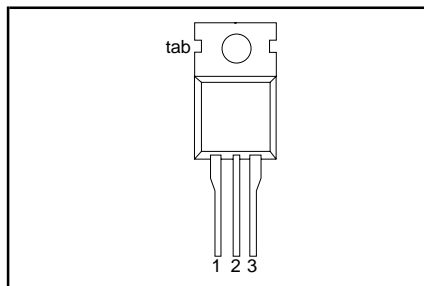
## QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$V_{CESM}$	Collector-emitter voltage peak value	$V_{BE} = 0 \text{ V}$	-	1000	V
$V_{CEO}$	Collector-emitter voltage (open base)		-	450	V
$I_C$	Collector current (DC)		-	5	A
$I_{CM}$	Collector current peak value		-	10	A
$P_{tot}$	Total power dissipation	$T_{mb} \leq 25 \text{ }^\circ\text{C}$	-	100	W
$V_{CESat}$	Collector-emitter saturation voltage	$I_C = 2.5 \text{ A}; I_B = 0.33 \text{ A}$	-	1.5	V
$I_{CSat}$	Collector Saturation current		2.5		A
$t_f$	Inductive fall time	$I_{Con} = 2.5 \text{ A}; I_{Bon} = 0.5 \text{ A}$	0.08	0.15	$\mu\text{s}$

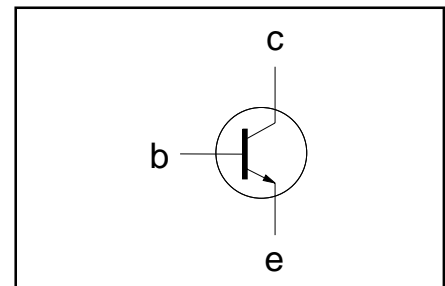
## PINNING - TO220AB

PIN	DESCRIPTION
1	base
2	collector
3	emitter
tab	collector

## PIN CONFIGURATION



## SYMBOL



## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CESM}$	Collector-emitter voltage peak value	$V_{BE} = 0 \text{ V}$	-	1000	V
$V_{CEO}$	Collector-emitter voltage (open base)		-	450	V
$I_C$	Collector current (DC)		-	5	A
$I_{CM}$	Collector current peak value		-	10	A
$I_B$	Base current (DC)		-	2	A
$I_{BM}$	Base current peak value		-	4	A
$P_{tot}$	Total power dissipation	$T_{mb} \leq 25 \text{ }^\circ\text{C}$	-	100	W
$T_{stg}$	Storage temperature		-65	150	$^\circ\text{C}$
$T_j$	Junction temperature		-	150	$^\circ\text{C}$

## THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Junction to mounting base		-	1.25	K/W
$R_{th\ j-a}$	Junction to ambient	in free air	-	60	K/W

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BUT11AI

**STATIC CHARACTERISTICS** $T_{mb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CES}$	Collector cut-off current <sup>1</sup>	$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$	-	-	1.0	mA
$I_{CES}$		$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $T_j = 125\text{ }^{\circ}\text{C}$	-	-	2.0	mA
$I_{EBO}$	Emitter cut-off current	$V_{EB} = 9.0\text{ V}; I_C = 0\text{ A}$	-	-	10.0	mA
$V_{CEO\text{sust}}$	Collector-emitter sustaining voltage	$I_B = 0\text{ A}; I_C = 100\text{ mA};$ $L = 25\text{ mH}$	450	-	-	V
$V_{CE\text{sat}}$	Collector-emitter saturation voltage	$I_C = 2.5\text{ A}; I_B = 0.33\text{ A}$	-	-	1.5	V
$V_{BE\text{sat}}$	Base-emitter saturation voltage	$I_C = 2.5\text{ A}; I_B = 0.33\text{ A}$	-	-	1.3	V
$h_{FE}$	DC current gain	$I_C = 5\text{ mA}; V_{CE} = 5\text{ V}$	10	20	35	
$h_{FE}$		$I_C = 0.5\text{ A}; V_{CE} = 5\text{ V}$	14	22	35	
$h_{FE\text{sat}}$		$I_C = 2.5\text{ A}; V_{CE} = 5\text{ V}$	9	13	17	

**DYNAMIC CHARACTERISTICS** $T_{mb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$t_{on}$	Switching times resistive load Turn-on time	$I_{Con} = 2.5\text{ A}; I_{Bon} = 0.5\text{ A}; -I_{Boff} = 0.5\text{ A}$	0.6 3.4 0.6	1.0	$\mu\text{s}$
$t_s$	Turn-off storage time		-	4.0	$\mu\text{s}$
$t_f$	Turn-off fall time		-	0.8	$\mu\text{s}$
	Switching times inductive load	$I_{Con} = 2.5\text{ A}; I_{Bon} = 0.5\text{ A}; L_B = 1\text{ }\mu\text{H};$ $-V_{BB} = 5\text{ V}$			
$t_s$	Turn-off storage time		1.1	1.4	$\mu\text{s}$
$t_f$	Turn-off fall time		80	150	ns
$t_s$	Turn-off storage time	$I_{Con} = 2.5\text{ A}; I_{Bon} = 0.5\text{ A}; L_B = 1\text{ }\mu\text{H};$ $-V_{BB} = 5\text{ V}; T_j = 100\text{ }^{\circ}\text{C}$	1.2	1.5	$\mu\text{s}$
$t_f$	Turn-off fall time		140	300	ns

**[INCLUDE]**<sup>1</sup> Measured with half sine-wave voltage (curve tracer).

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**MECHANICAL DATA**

*Dimensions in mm*

*Net Mass: 2 g*

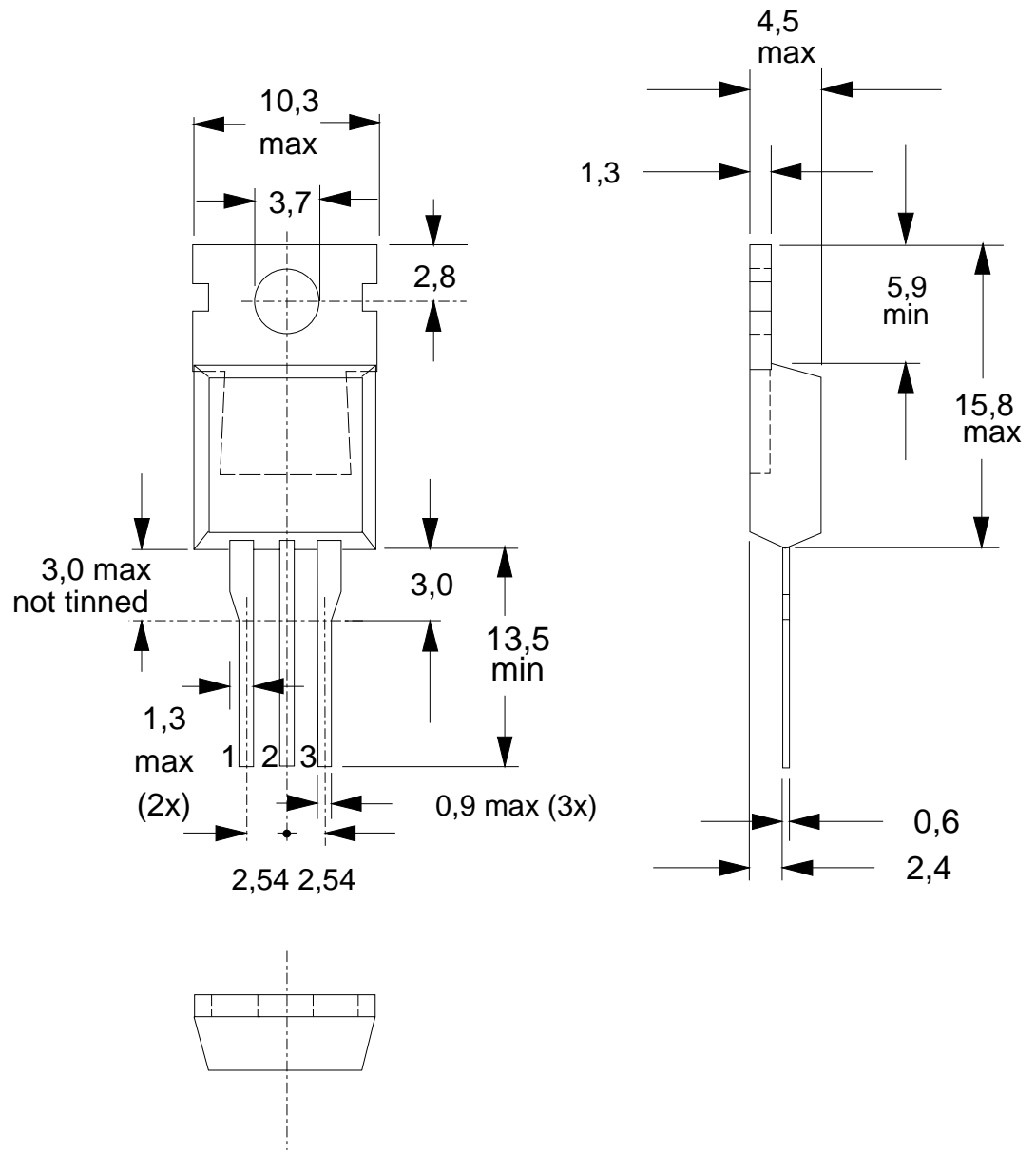


Fig.1. TO220AB; pin 2 connected to mounting base.

**Notes**

1. Refer to mounting instructions for TO220 envelopes.
2. Epoxy meets UL94 V0 at 1/8".

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**DEFINITIONS**

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	
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